

# TPCF8305

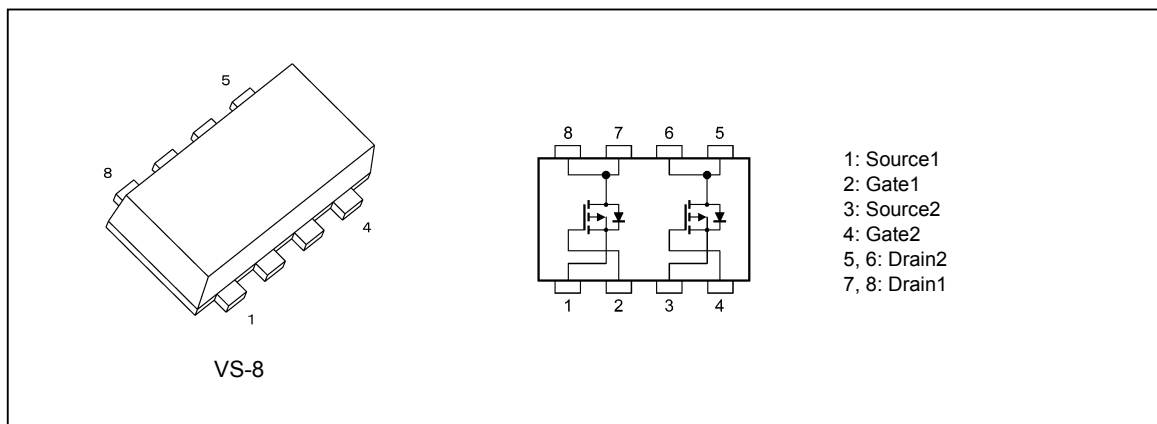
## 1. Applications

- Notebook PCs
- Mobile Handsets

## 2. Features

- (1) Small footprint due to a small and thin package
- (2) Low drain-source on-resistance:  $R_{DS(ON)} = 47 \text{ m}\Omega$  (typ.) ( $V_{GS} = -4.5 \text{ V}$ )
- (3) Low leakage current:  $I_{DSS} = -10 \text{ }\mu\text{A}$  (max) ( $V_{DS} = -20 \text{ V}$ )
- (4) Enhancement mode:  $V_{th} = -0.5$  to  $-1.2 \text{ V}$  ( $V_{DS} = -10 \text{ V}$ ,  $I_D = -0.2 \text{ mA}$ )

## 3. Packaging and Internal Circuit



## 4. Absolute Maximum Ratings (Note) ( $T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	$V_{DSS}$	-20	V
Gate-source voltage	$V_{GSS}$	$\pm 12$	
Drain current (DC)	$I_D$	-4	A
Drain current (pulsed)	$I_{DP}$	-16	
Power dissipation (single operation)	$P_{D(1)}$	1.35	W
Power dissipation (per device for dual operation)	$P_{D(2)}$	1.12	
Power dissipation (single operation)	$P_{D(1)}$	0.53	
Power dissipation (per device for dual operation)	$P_{D(2)}$	0.33	
Single-pulse avalanche energy	$E_{AS}$	10.4	mJ
Avalanche current	$I_{AR}$	-4	A
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

**5. Thermal Characteristics**

Characteristics			Symbol	Max	Unit
Channel-to-ambient thermal resistance (single operation)	(t = 5 s)	(Note 2), (Note 4)	$R_{th(ch-a)(1)}$	92.5	°C/W
Channel-to-ambient thermal resistance (per device for dual operation)	(t = 5 s)	(Note 2), (Note 5)	$R_{th(ch-a)(2)}$	111.6	
Channel-to-ambient thermal resistance (single operation)	(t = 5 s)	(Note 3), (Note 4)	$R_{th(ch-a)(1)}$	235.8	
Channel-to-ambient thermal resistance (per device for dual operation)	(t = 5 s)	(Note 3), (Note 5)	$R_{th(ch-a)(2)}$	378.7	

Note 1: Ensure that the channel temperature does not exceed 150°C.

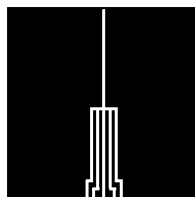
Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 4: Power dissipation and thermal resistance values per device with the other device being off (During single operation, power is supplied to only one of the two devices.)

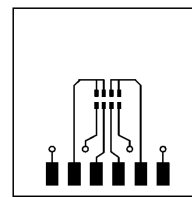
Note 5: Power dissipation and thermal resistance values per device for dual operation (During dual operation, power is evenly supplied to both devices.)

Note 6:  $V_{DD} = -16\text{ V}$ ,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 0.5\text{ mH}$ ,  $R_G = 25\ \Omega$ ,  $I_{AR} = -4\text{ A}$



FR-4  
25.4 × 25.4 × 0.8  
(Unit: mm)

**Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)**



FR-4  
25.4 × 25.4 × 0.8  
(Unit: mm)

**Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)**

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

**6. Electrical Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)**

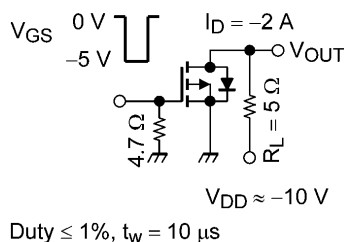
**6.1. Static Characteristics**

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±12 V, V <sub>DS</sub> = 0 V	—	—	±0.1	μA
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = -20 V, V <sub>GS</sub> = 0 V	—	—	-10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 0 V	-20	—	—	V
Drain-source breakdown voltage (Note 7)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 8 V	-12	—	—	
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -0.2 mA	-0.5	—	-1.2	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = -1.8 V, I <sub>D</sub> = -1 A	—	125	265	mΩ
		V <sub>GS</sub> = -2.0 V, I <sub>D</sub> = -2 A	—	95	160	
		V <sub>GS</sub> = -2.5 V, I <sub>D</sub> = -2 A	—	65	83	
		V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -2 A	—	47	58	

Note 7: If a forward bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drain-source breakdown voltage is lowered in this mode.

**6.2. Dynamic Characteristics**

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	—	680	—	pF
Reverse transfer capacitance	C <sub>rss</sub>		—	85	—	
Output capacitance	C <sub>oss</sub>		—	108	—	
Switching time (rise time)	t <sub>r</sub>	See Figure 6.2.1.	—	8.7	—	ns
Switching time (turn-on time)	t <sub>on</sub>		—	16	—	
Switching time (fall time)	t <sub>f</sub>		—	18	—	
Switching time (turn-off time)	t <sub>off</sub>		—	70	—	



**Fig. 6.2.1 Switching Time Test Circuit**

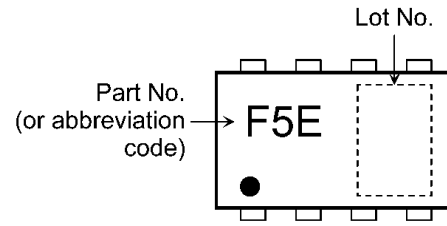
**6.3. Gate Charge Characteristics**

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q <sub>g</sub>	V <sub>DD</sub> ≈ -16 V, V <sub>GS</sub> = -5 V, I <sub>D</sub> = -4 A	—	9.2	—	nC
Gate-source charge 1	Q <sub>gs1</sub>		—	1.8	—	
Gate-drain charge	Q <sub>gd</sub>		—	2.0	—	

**6.4. Source-Drain Characteristics**

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Pulsed reverse drain current (Note 8)	I <sub>DRP</sub>	—	—	—	-16	A
Diode forward voltage	V <sub>DSF</sub>	I <sub>DR</sub> = -4 A, V <sub>GS</sub> = 0 V	—	—	1.2	V

Note 8: Ensure that the channel temperature does not exceed 150°C.

**7. Marking****Fig. 7.1 Marking**

8. Characteristics Curves (Note)

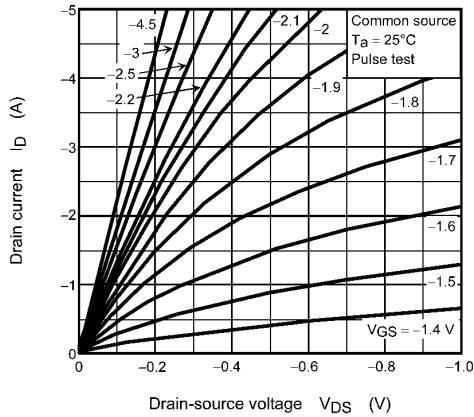


Fig. 8.1  $I_D - V_{DS}$

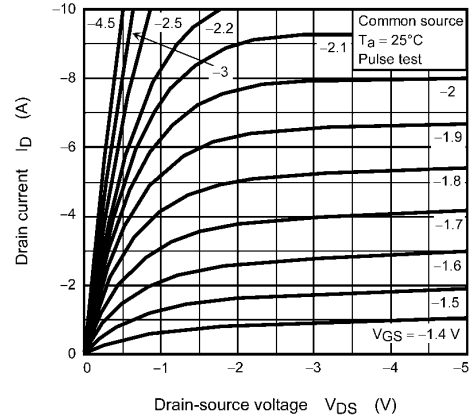


Fig. 8.2  $I_D - V_{DS}$

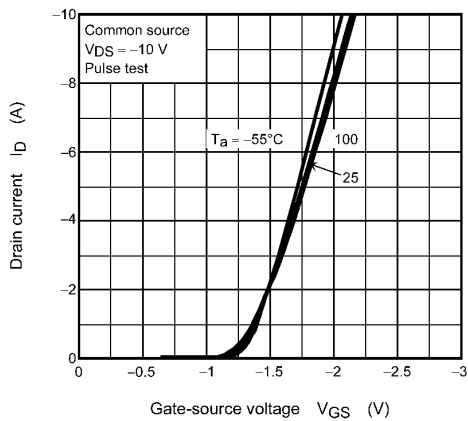


Fig. 8.3  $I_D - V_{GS}$

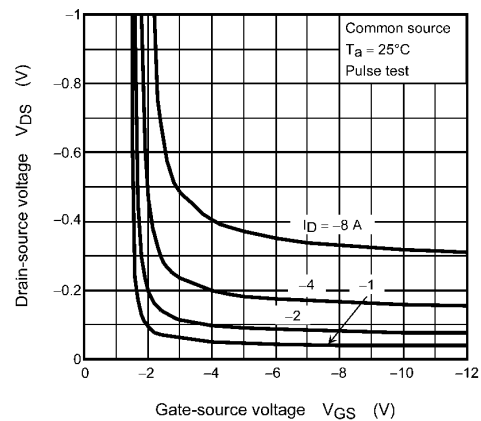


Fig. 8.4  $V_{DS} - V_{GS}$

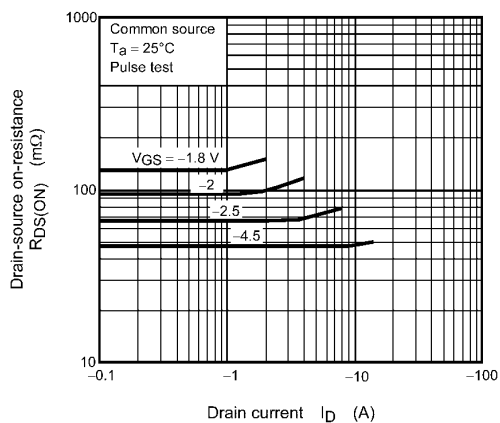


Fig. 8.5  $R_{DS(ON)} - I_D$

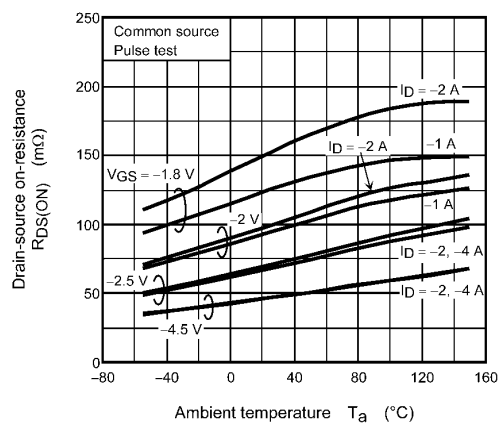


Fig. 8.6  $R_{DS(ON)} - T_a$

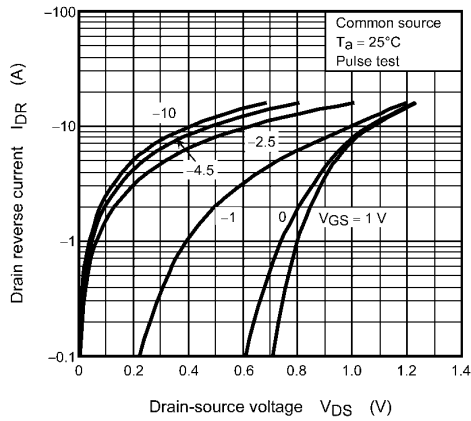


Fig. 8.7  $I_{DR} - V_{DS}$

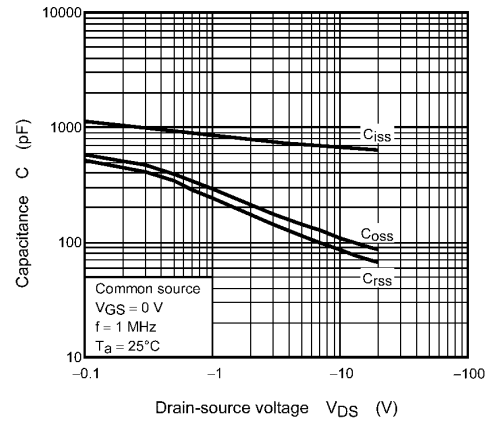


Fig. 8.8 Capacitance -  $V_{DS}$

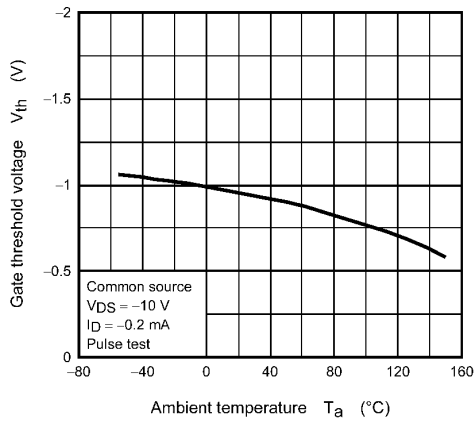


Fig. 8.9  $V_{th} - T_a$

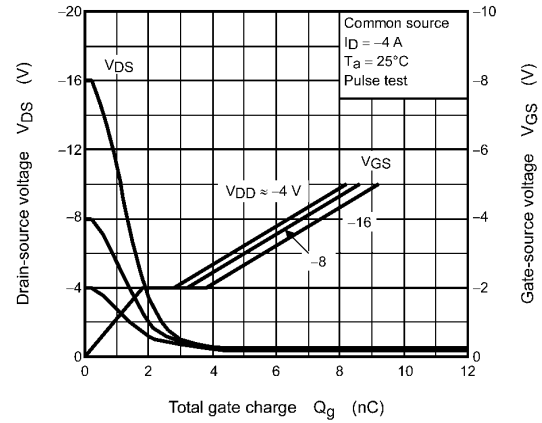


Fig. 8.10 Dynamic Input/Output Characteristics

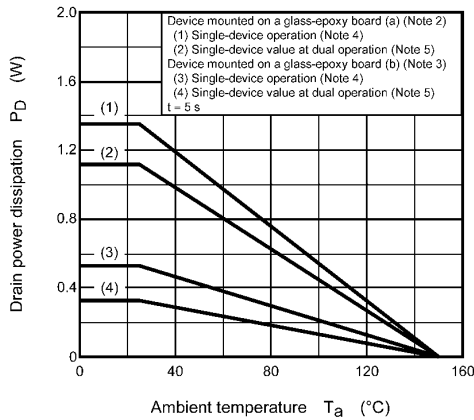
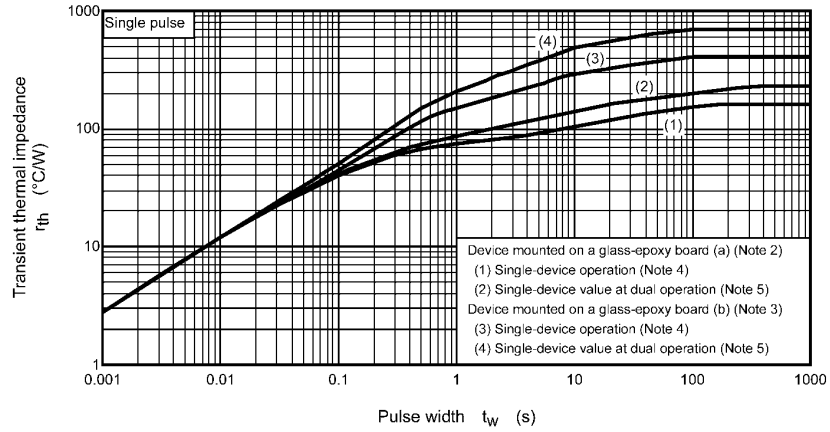
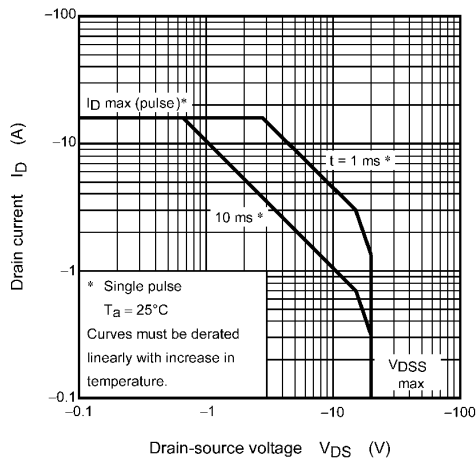


Fig. 8.11  $P_D - T_a$   
 (Guaranteed Maximum)



**Fig. 8.12  $r_{th} - t_w$**   
(Guaranteed Maximum)

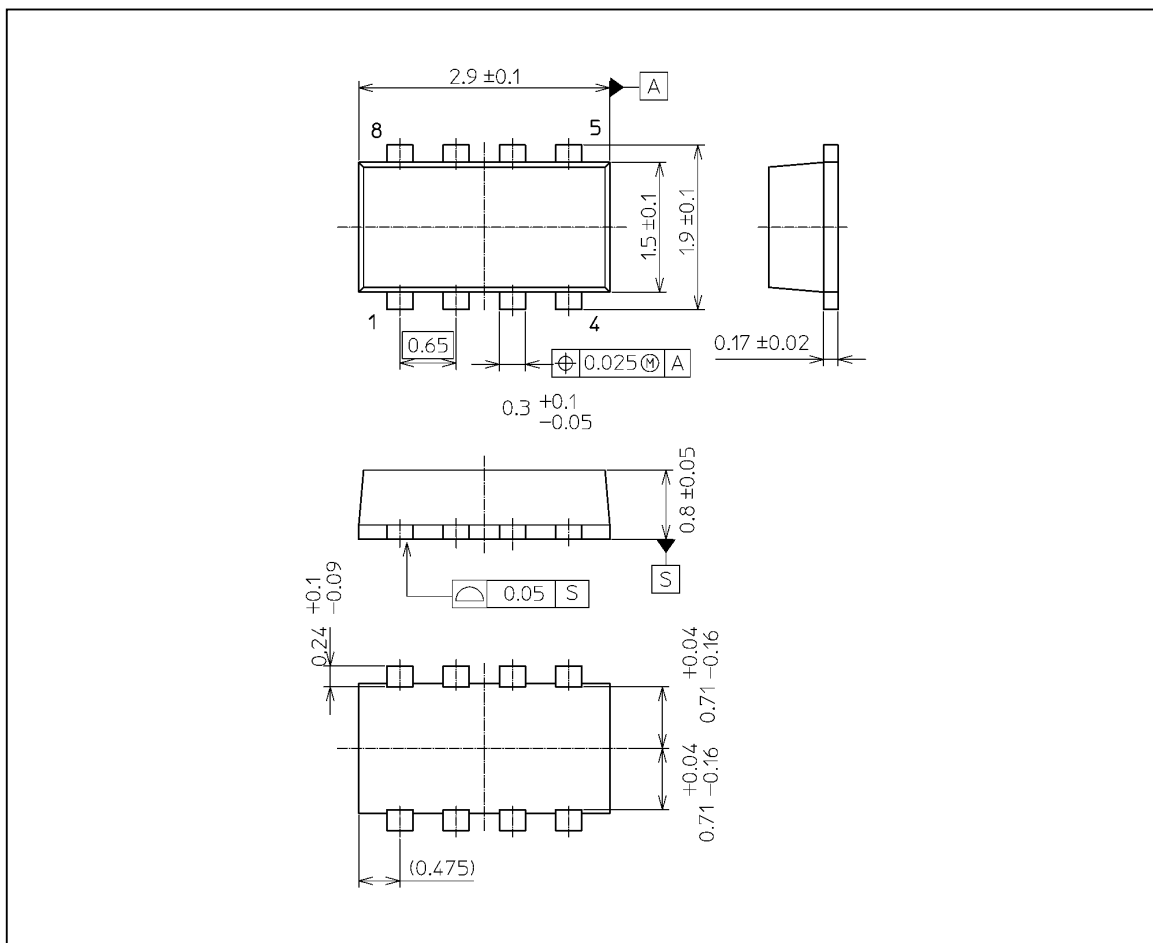


**Fig. 8.13 Safe Operating Area**  
(Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

**Package Dimensions**

Unit: mm



Weight: 0.011 g (typ.)

Package Name(s)
TOSHIBA: 2-3U1S
Nickname: VS-8



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